Title (en)

IMAGE DISPLAY SCREEN AND METHOD OF ADDRESSING SAID SCREEN

Title (de)

BILDANZEIGESCHIRM UND VERFAHREN ZUR ADRESSIERUNG DES SCHIRMS

Title (fr)

ECRAN D'AFFICHAGE D'IMAGES ET PROCEDE D'ADRESSAGE DE CET ECRAN

Publication

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Application

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Priority

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Abstract (en)

[origin: WO2005073948A1] The invention relates to a display screen comprising: light emitters (4) which are distributed in rows and columns of emitters; and a first addressing circuit (6, 14, 16, 18) which is associated with each emitter of the network, said circuit (6) comprising a first current modulator (14) which can power the emitter (4) and a first storage capacity (16) which can store a potential at the grid electrode of the first current modulator (14). The inventive screen comprises at least one second emitter addressing circuit (12, 34, 36, 38), said first and second addressing circuits being associated with the same emitter. In addition, the second circuit comprises a second current modulator (34) for the emitter and a second storage capacity (36) which can store a potential at the grid electrode of the second current modulator. The invention also relates to a method of addressing the screen.

IPC 8 full level

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Citation (examination)

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